



SOT-323 Plastic-Encapsulated Diode

MMBD4448W SWITCHING DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

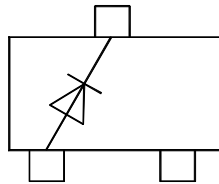
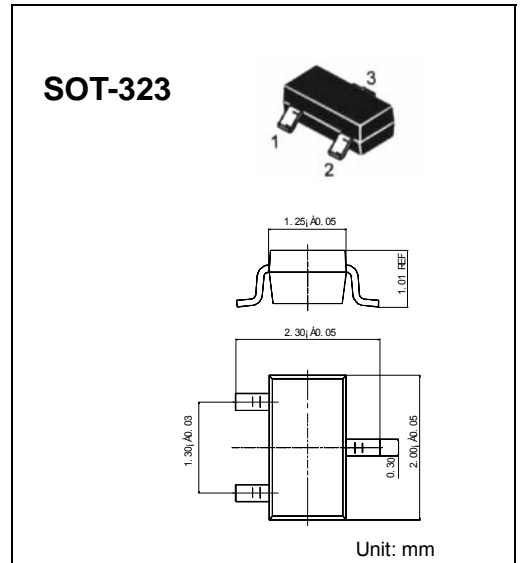
I_O : 250 mA

Collector-base voltage

V_R : 75 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$



Marking: KA3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu\text{A}$	75		V
Reverse voltage leakage current	I_R	$V_R=20\text{V}$ $V_R=75\text{V}$		0.025 2.5	μA
Forward voltage	V_F	$I_F=5\text{mA}$ $I_F=10\text{mA}$ $I_F=100\text{mA}$ $I_F=150\text{mA}$		0.72 0.855 1 1.25	V
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		4	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	nS

Test period $<3000\mu\text{s}$.